

**EAST Search History****EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("5948470").PN. or ((2002/042027) or (2002/005391)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 12:45
S2	0	(2002/042027).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:35
S3	0	2002/042027	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:35
S4	0	2002/042027	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:36
S5	0	(stephen chou).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:36
S6	4	("2002042027").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:37
S7	89	(stephen near chou).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:43
S8	0	S7 and @pd="02200411"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:44

S9	0	(2002/0005391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:46
S10	0	(2002/005391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:46
S11	0	2002/005391	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:46
S12	0	2002/0005391	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:47
S13	0	thurn-albrecht.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:47
S14	10	(thurn-albrecht).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:48
S15	75	"5948470"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:50
S16	2	("5948470").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:50
S17	0	(wo01/33300).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:50

S18	20	01/33300	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:51
S19	0	("wo20010500").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:52
S20	117005	"20010500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S21	0	wo?20010500	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S22	0	wo20010500	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S23	2	("7082876").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:54
S24	0	WO "20010500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:26
S25	0	method of reducing pattern distortions during imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:30
S26	15	reducing pattern distortions during imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:31

S27	1	wo-0133300-\$ did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:32
S28	2	de-10030016-\$ did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:34
S29	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:04
S30	1308003	template or mold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:05
S31	7481	S30 near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:06
S32	289533	silicon near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:06
S33	436	S31 with (polymer or pmma or pmgi or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:07
S34	168	S29 and S30 and S33	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:07
S35	798153	nanometer or nm or nanoprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:09

S36	48	S34 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:09
S37	28	S29 and S33 and S32 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:14
S38	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:06
S39	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:06
S40	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:07
S41	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:08
S42	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:09
S43	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S44	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11

S45	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S46	0	S43 and S44 and s "40" and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S47	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S48	322	S43 and S44 and S47 and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S49	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:12
S50	93	S48 and S49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:12
S51	28	S50 and (pmma or polymer or photoresist or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:13
S52	226110	template	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:32
S53	55209	S52 and "43" and "45" and "51"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:33

S54	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S55	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S56	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S57	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S58	322	S54 and S55 and S57 and S56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S59	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S60	93	S58 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S61	28	S60 and (pmma or polymer or photoresist or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S62	0	S52 and S54 and S56 and S61	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34

S63	463	(silicon near substrate) and (polymer or pmma or pmgi or photoresist) and (semiconductor near (ge or germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:36
S64	159	S63 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:37
S65	13	S60 and (pmma or polymer or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:47
S66	346	S59 and S56 and S52 and S57 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:48
S67	4630	((nano?imprint\$3) or (nano imprint \$3) or (imprint adj lithograp\$6)) or nanolithograp\$5 or (nano?lithogra \$6))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:34
S68	1602236	germanium or ge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:35
S69	268466	(pmma or polymethylmeth\$ or pmgi or polymethylgluta\$ or az5214e or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S70	1112	S67 and S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S71	101	S67 same S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38

S72	1540	S67 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:41
S73	480	S67 same S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S74	26586	S68 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S75	3507	S68 same S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S76	10	S71 and S73 and S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S77	65	shunpu.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S78	19543	template.ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S79	4	S78 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S80	3	("4407695"   "4512848"   "4801476").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/21 12:38
S81	34806	germanium with (aluminum or al or indium or gold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:15

S82	5375	(germanium with (aluminum or al or indium or gold)) with semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:16
S83	30322507	@ad<"20050513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S84	3671	S82 and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S85	92	S84 and substrate and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S86	505	((germanium with (aluminum or al or indium or gold)) with semiconductor) with substrate) and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:31
S87	938302	"427".clas. or "428".clas. or "430".clas. or "425".clas. or "264".clas. or "156".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:35
S88	572282	S83 and S87	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:36
S89	2	("4512848").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/21 14:41
S90	483	photoresist and template and silicon and germanium and S69 and pattern and (nanometer or angstrom or nm )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:03

S91	108	S90 and S88	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:04
S92	108	S91 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:13
S93	268466	(pmma or polymethylmeth\$ or pmgi or polymethylgluta\$ or az5214e or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S94	30322507	@ad<"20050513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S95	938302	"427".clas. or "428".clas. or "430".clas. or "425".clas. or "264".clas. or "156".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S96	572282	S94 and S95	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S97	483	photoresist and template and silicon and germanium and S93 and pattern and (nanometer or angstrom or nm )	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S98	108	S97 and S96	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S99	108	S98 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12

S100	34	S99 and (imprint with lithography)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S101	34	(US-20060076717-\$ or US-20060062867-\$ or US-20060035164-\$ or US-20040141168-\$ or US-20040124566-\$ or US-20040086793-\$ or US-20040053146-\$ or US-20040022888-\$ or US-20040021254-\$ or US-20040007799-\$ or US-20030205658-\$ or US-20030205657-\$ or US-20020115002-\$ or US-20020098426-\$ or US-20020094496-\$ or US-20020093122-\$).did. or (US-7374968-\$ or US-7338275-\$ or US-7229273-\$ or US-7179079-\$ or US-7140861-\$ or US-7132225-\$ or US-7077992-\$ or US-7070405-\$ or US-7037639-\$ or US-7027156-\$ or US-6954275-\$ or US-6932934-\$ or US-6926921-\$ or US-6921615-\$ or US-6919152-\$ or US-6916585-\$ or US-6916584-\$ or US-6696220-\$).did.	US-PGPUB; USPAT	ADJ	ON	2008/07/21 17:28
S102	34	S101 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:29
S103	1	S102 not (silicon adj germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:31
S104	1	S103 and germanium and S93 and S97	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:35
S105	13	("20030213382"   "20040163758"   "5512131"   "6060121"   "6365059"   "6407443"   "6518194"   "6547940"   "6599824"   "6709929"   "6755984"   "6764833"   "7060625").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/22 07:59

S106	5	"6506660"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 08:08
S107	34	(US-20060076717-\$ or US-20060062867-\$ or US-20060035164-\$ or US-20040141168-\$ or US-20040124566-\$ or US-20040086793-\$ or US-20040053146-\$ or US-20040022888-\$ or US-20040021254-\$ or US-20040007799-\$ or US-20030205658-\$ or US-20030205657-\$ or US-20020115002-\$ or US-20020098426-\$ or US-20020094496-\$ or US-20020093122-\$).did. or (US-7374968-\$ or US-7338275-\$ or US-7229273-\$ or US-7179079-\$ or US-7140861-\$ or US-7132225-\$ or US-7077992-\$ or US-7070405-\$ or US-7037639-\$ or US-7027156-\$ or US-6954275-\$ or US-6932934-\$ or US-6926921-\$ or US-6921615-\$ or US-6919152-\$ or US-6916585-\$ or US-6916584-\$ or US-6696220-\$).did.	US-PGPUB; USPAT	ADJ	ON	2008/07/22 09:59
S108	34	S107 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 09:59
S109	1666	germanium with sputter\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 10:17
S110	26	S109 and silicon and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 10:17
S111	34	S107 and nm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:33

S112	16	S107 and (layer with nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:34
S113	7	S107 and ((thick or thickness) with nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:37
S114	0	S107 and ((thick or thickness) with (mask or polymer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:39
S115	0	S107 and ((thick or thickness) with (resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:39
S116	4	S107 and ((thick or thickness) with (\$resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:40
S117	3	S107 and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:03
S118	1	S107 and polymethylmethacrylate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:04
S119	25	(US-20020042027-\$ or US-20020005391-\$ or US-20030205658-\$ or US-20030205657-\$ or US-20050281982-\$ or US-20050221218-\$ or US-20040141168-\$ or US-20040124566-\$ or US-20040086793-\$ or US-20040053146-\$ or US-20040053009-\$ or US-20020168592-\$ or US-20020115002-\$ or US-20020094496-\$ or US-20060035164-\$ or US-20040170925-\$).did. or (US-5948470-\$ or US-6753130-\$ or US-4512848-\$ or US-7374968-\$ or US-	US-PGPUB; USPAT; DERWENT	ADJ	ON	2008/07/22 13:07

		7060625-\$ or US-6755984-\$ or US-6365059-\$ or US-5512131-\$).did. or (US-5948470-\$ or WO-0133300-A-\$ or DE-10030016-A-\$).did.				
S120	10	S119 and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:08
S121	23	S119 and nm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:15
S122	1	("20030071016").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/22 16:23
S123	199	(lee near heon).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:42
S124	15	S123 and silicon and substrate and pattern and imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:43
S125	177981	"430".clas. or "216".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:47
S126	533	S125 and silicon and substrate and pattern and imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:47
S127	190	S126 and template	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:48
S128	32	S127 and imprint pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:49

S129	5	2003/0071016	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:52
S130	2	"20030071016"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:52
S131	456	nano?imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:00
S132	17	S131 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:01
S133	53	"6165911"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:05
S134	4	"6673714"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:07
S135	12064	"Hewlett-Packard Development ". asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
S136	53	"6165911"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
S137	17	S135 and S136	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32

S138	456	nano?imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S139	17	S138 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S140	0	S135 and S139	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S141	15	S135 and S138	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
S142	5	S135 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:34
S143	202	ingenia.asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 08:41
S144	136401	S143 and semiconductor or imprint or lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 08:42
S145	12	S143 and (semiconductor or imprint or lithography)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 08:42
S146	23	((SHUNPU) near2 (LI)).INV.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/23 09:50
S147	32	((SHUNPU) near2 (LI)).INV.	EPO; JPO; DERWENT	ADJ	ON	2008/07/23 09:51
S148	55	S146 or S147	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 09:51

S149	22523	(single?phase)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:18
S150	72	(single?phase polymer)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:18
S151	1	(single?phase plastic)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:19
S152	32	(single?phase layer)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:19
S153	105	S150 or S151 or S152	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:19
S154	4559269	@ad<"20031211"	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:20
S155	84	S153 and S154	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:20
S156	26	S155 and substrate	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:21
S157	0	S155 and template	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:21
S158	27	shunpu.inv.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:22
S159	60563	(single phase) or (single-phase)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:24
S160	219	(single phase polymer) or (single-phase polymer)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S161	9	(single phase plastic) or (single-phase plastic)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S162	228	S160 or S161	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S163	65	S162 and (template or substrate)	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:25
S164	30	S163 and S154	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:26
S165	0	S164 and shunpu.inv.	US-PGPUB; USPAT; USOCR	ADJ	OFF	2009/01/05 07:26
S166	37	substrate and pmmi	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:55
S167	25887	substrate and polymer and (texture or textured)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:57
S168	318158	tg or glass transition	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:57
S169	7874	below (tg or glass transition)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:58
S170	509	S167 and S169	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:58
S171	37644	polymer layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:59
S172	122	S170 and S171	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 14:59

S173	25	(US-20020042027-\$ or US-20020005391-\$ or US-20030205658-\$ or US-20030205657-\$ or US-20050281982-\$ or US-20050221218-\$ or US-20040141168-\$ or US-20040124566-\$ or US-20040086793-\$ or US-20040053146-\$ or US-20040053009-\$ or US-20020168592-\$ or US-20020115002-\$ or US-20020094496-\$ or US-20060035164-\$ or US-20040170925-\$).did. or (US-5948470-\$ or US-6753130-\$ or US-4512848-\$ or US-7374968-\$ or US-7060625-\$ or US-6755984-\$ or US-6365059-\$ or US-5512131-\$).did. or (US-5948470-\$ or WO-0133300-A-\$ or DE-10030016-A-\$).did.	US-PGPUB; USPAT; DERWENT	ADJ	ON	2009/04/30 15:14
S174	1	S173 and S169	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:15
S175	6	S173 and S168	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:15
S176	245154	"428".clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:19
S177	55	S172 and S176	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:19
S178	0	("2005/0281982").URPN.	USPAT	ADJ	ON	2009/04/30 15:30
S179	2110815	template or stamp or stamper or press or die or mold	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S180	2589840	layer or substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S181	1012394	polymer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S182	324457	S179 and S180 and S181	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:31
S183	3298	S182 and S169	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:33
S184	451	S183 and S171	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:34
S185	3	S184 and "249".clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/04/30 15:36
S186	91799	germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:57
S187	35821	pmma	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:57
S188	1731	S186 and S187	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:57
S189	48253	germanium and semiconductor and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S190	1098	S188 and S189	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58

S191	83956	texture and (bake or baking or heat or heating or heated)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S192	63	S190 and S191	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 08:58
S193	0	master and resist and germanium and (@ay<"2003" or @prad<"20030101" or @py<"2003")	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:36
S194	0	master and resist and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:36
S195	2760	master and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S196	734	S195 and resist	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S197	393	S196 and (@ay<"2003" or @prad<"20030101" or @py<"2003")	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S198	73	S197 and pmma	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:37
S199	67	S198 and (heat or temperature or bake or heated or baked)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:38
S200	67	S199 and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:39
S201	1	S199 and pmma layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:39
S202	6	("4098917"   "4127414"   "4188215"   "4256825"   "4269935"   "4276368").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/01 09:40
S203	18	("4373018").URPN.	USPAT	ADJ	ON	2009/05/01 09:41
S204	109	977/887.ccls.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:47
S205	156504	substrate and (anneal or anneal\$)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:48
S206	5	S204 and S205	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:48
S207	2619	S205 and pmma	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:56
S208	20706	S205 and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:57
S209	2784	germanium near substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:57
S210	1274	S208 and S209	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:57
S211	3530331	(heat or temperature or bake or heated or baked)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:58
S212	1189	S210 and S211	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:58
S213	154	S212 and polymer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 10:59
S214	266679	textu\$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:00

S215	170767	texture	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:00
S216	10	S213 and S214	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:00
S218	1850800	template or imprint or stamp or press or mask	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:03
S219	130	S213 and S218	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 11:03
S220	5079	S208 and polymer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 12:03
S221	373	S220 and polymer layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 12:03
S222	144062	S205 and S211	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 13:03
S223	2820	S222 and polymer layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 13:03
S224	362	S223 and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 13:03
S225	1488	425/385.ccls.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:37
S226	10	S225 and germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:37
S227	20	S225 and anneal\$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:40
S228	32	("20020185584"   "20030080458"   "20030209819"   "20040029041"   "20040036201"   "20040039090"   "20040131718"   "20040146792"   "20040169861"   "20040233442"   "20040233443"   "20040233444"   "20040259279"   "20050067379"   "20050133954"   "20050179149"   "20060183060"   "5204126"   "6429932"   "6517995"   "6607173"   "6632342"   "6656393"   "6713238"   "6921630"   "6936181"   "6949199"   "7013064"   "7070405"   "7077992"   "7136150"   "7235474").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/05 14:52
S229	4622	((425/171) or (425/174) or (425/174.4) or (264/1.38) or (425/385) or (425/169) or (425/173)).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/12 10:03
S230	97200	pmgi or polymethylgluta\$ or poly methyl glutar\$ or polymethyl glutar \$ or poly methylglutar\$ or pmma or poly methyl methacrylate or poly methylmethacrylate or polymethyl methacrylate or polymethylmethacrylate or (photoresist (az-5214\$ or az5214 or az "5214"\$ or az-5214 or az "5214" or az5214))	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 10:27
S231	92066	germanium	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 10:27

S232	7	S229 and S230 and S231	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 10:27
S233	241280	anneal or anneal\$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:25
S234	4622	((425/171) or (425/174) or (425/174.4) or (264/1.38) or (425/385) or (425/169) or (425/173)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/12 12:25
S235	97200	pmgi or polymethylgluta\$ or poly methyl glutar\$ or polymethyl glutar \$ or poly methylglutar\$ or pmma or poly methyl methacrylate or poly methylmethacrylate or polymethyl methacrylate or polymethylmethacrylate or (photoresist (az-5214\$ or az5214\$ or az "5214"\$ or az-5214 or az "5214" or az5214))	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:26
S236	24	S233 and S234 and S235	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:26
S237	156837	S233 and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 12:42
S238	49764	S237 and (mold or template or stamp or stamper)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 13:02
S239	2676	S238 and S235	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 13:02
S240	13	S239 and S234	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 13:02
S241	8129	S233 near (polymer or plastic or template or semiconductor or mold)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:30
S242	275	S241 and ("264".clas. or "425". clas.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:30
S243	0	(2002/0042027).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/12 14:44
S244	58	2002/0042027	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:44
S245	0	2002/0042027.pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 14:46
S246	541	"5772905"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 15:01
S247	1	"5772905".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 15:01
S248	1	"6849558".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:24
S249	1	"6755984".pn.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:26
S250	103562	"10 nm" or "10nm"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:33
S251	3552	S250 near (substrate or layer or semiconductor or germanium or silicon or wafer)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:33
S252	40	S251 and chou	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:34

S253	131	"5259926"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:37
S254	940	S250 near (substrate or semiconductor or germanium or silicon or wafer)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:44
S255	332	S250 near substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:44
S256	65	S250 near semiconductor	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:45
S257	1199	S250 and ("264".clas. or "425". clas.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:49
S258	1076	S257 and (substrate or layer or semiconductor)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S259	780	S258 and substrate	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S260	718	S259 and layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S261	280	S260 and semiconductor	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S262	79	S261 and chou	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:50
S263	5468	("10 nm" or "10nm") with semiconductor	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:52
S264	2526	("10 nm" or "10nm") with semiconductor with layer	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:52
S265	8	S264 and chou	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/12 16:52
S266	135	"6323108"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:09
S267	13	("5013681"   "5024723"   "5303255"   "5374564"   "5540785"   "5646058"   "5681775"   "5757038"   "5877070"   "5882987"   "5953620"   "5980633"   "6004865").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:39
S268	6	"5888297"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:42
S269	46	"4771016"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:46
S270	103562	("10 nm" or "10nm")	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:47
S271	6	S269 and S270	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 14:47
S272	5	"6030556"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/05/13 15:01

S273	26595	(( "3" or third or "3rd" or additional or another or extra or supporting or supportive) near3 (layer or lamina or level or coating or coated or coat or ply or overlay or sheet or zone)) and (semiconductor or semiconductive or semi conductor or semi?conductor or semi-conductor) and (polymer or pmma or polymethylmethacry\$ or poly?methylmethacry\$ or poly methylmethacryl\$ or polymethyl methacryl\$ or poly-methylmethacryl\$ or poly?methyl methacryl\$) and (template or stamp or stamper or press or pattern or imprint or imprinting or inprinted) and (nanometer or nm or nano-meter or nano?meter)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/01 11:18
S274	1	("6849558").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/01 11:48
S275	250124	anneal or anneal\$	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/01 12:29
S276	8424	S275 near (polymer or plastic or template or semiconductor or mold)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/01 12:29
S277	278	S276 and ("264".clas. or "425".clas.)	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/01 12:29
S278	4689	((425/171) or (425/174) or (425/174.4) or (264/1.38) or (425/385) or (425/169) or (425/173)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/10/01 12:29
S279	3945	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/01 12:30
S280	145874	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/01 12:30
S281	942303	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/01 12:30
S282	235313	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/01 12:30

S283	398	S279 and S280 and S282 and S281	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/10/01 12:30
S284	34	((SHUNPU) near2 (LI)).INV.	EPO; JPO; DERWENT	ADJ	ON	2009/10/01 12:30
S285	202371	@AD>"20090513" or @pd>"20090512" or @prad>"20090513"	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/01 12:33
S286	82	(S283 or S284 or S278 or S277) and S285	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/10/01 12:34
S287	2698	(428/450).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/04/13 18:43
S288	44	S287 and template	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/04/13 18:46
S289	54	S287 and (template or stamp)	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/04/13 18:47
S290	2698	(428/450).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/04/14 13:02
S291	54	S290 and (template or stamp)	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/04/14 13:02
S292	2085	S290 not S291	US-PGPUB; USPAT	ADJ	ON	2010/04/14 13:07

**EAST Search History (Interference)**

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**4/15/2010 11:52:45 AM****C:\Documents and Settings\dbrown\My Documents\EAST\Workspaces\10534931.wsp**